Supplementary Information

A Flexible Dual-gate Hetero-synaptic Transistor for Spatiotemporal Information Processing

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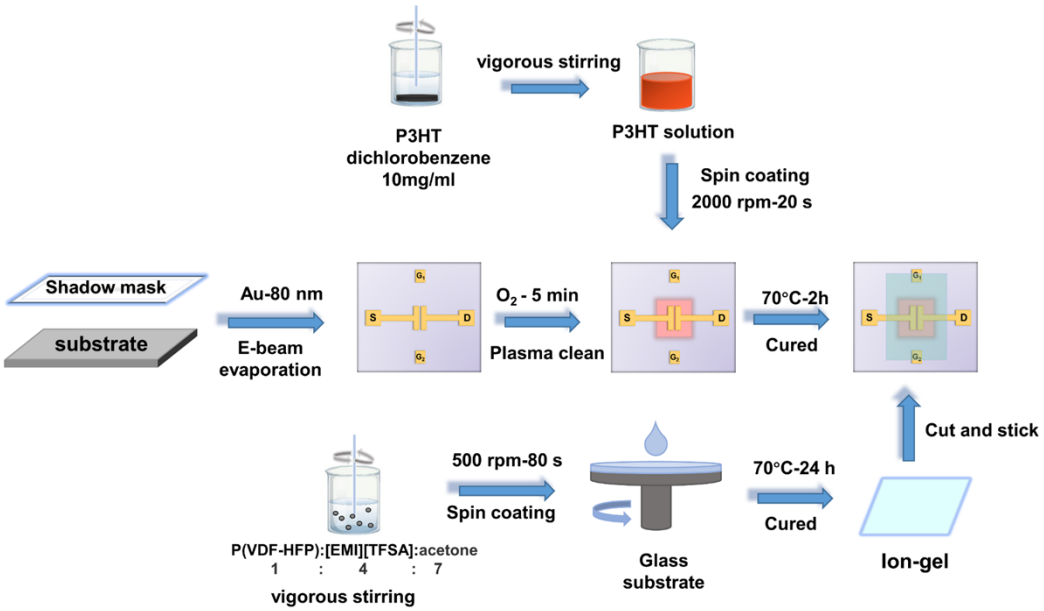

Figure S1. The flowchart showing the fabrication process of the transistor device.

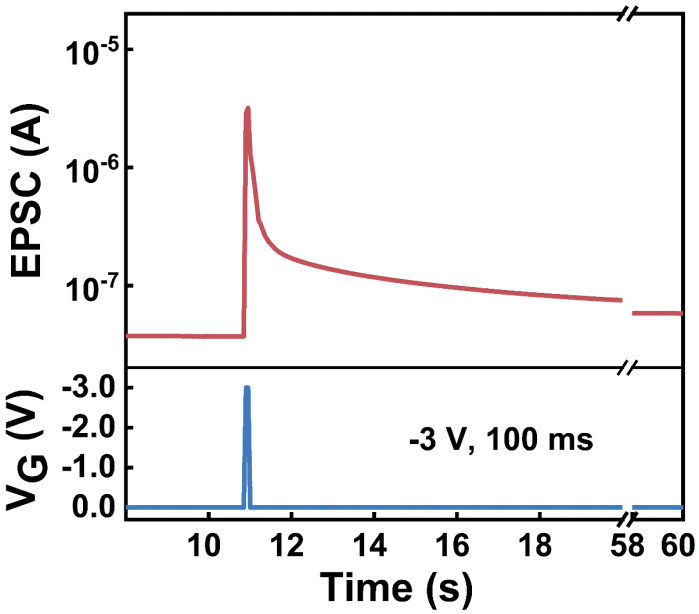

Figure S2 A typical LTP effect obtained in the electrolyte gated transistor triggered by an electric pulse (-3 V, 100 ms) applied on a single gate.

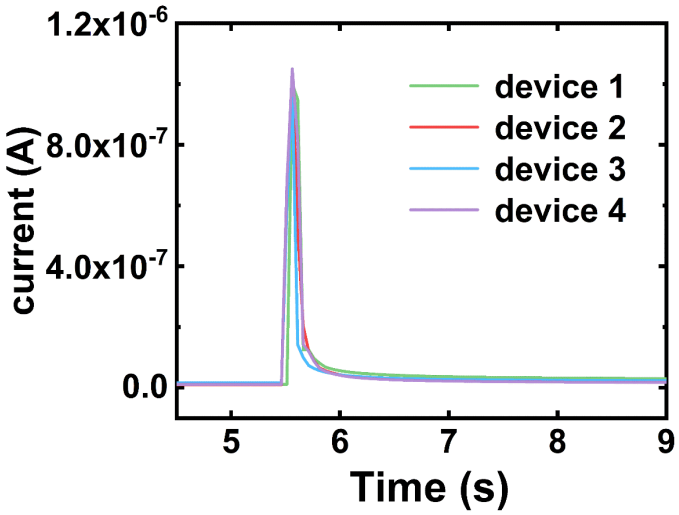

Figure S3 Current response of four P3HT based transistor devices to a single electric pulse (-1.5 V, 100 ms).